ne<mark>x</mark>peria

Important notice

Dear Customer,

On 7 February 2017 the former NXP Standard Product business became a new company with the tradename **Nexperia**. Nexperia is an industry leading supplier of Discrete, Logic and PowerMOS semiconductors with its focus on the automotive, industrial, computing, consumer and wearable application markets

In data sheets and application notes which still contain NXP or Philips Semiconductors references, use the references to Nexperia, as shown below.

Instead of <u>http://www.nxp.com</u>, <u>http://www.philips.com/</u> or <u>http://www.semiconductors.philips.com/</u>, use <u>http://www.nexperia.com</u>

Instead of sales.addresses@www.nxp.com or sales.addresses@www.semiconductors.philips.com, use **salesaddresses@nexperia.com** (email)

Replace the copyright notice at the bottom of each page or elsewhere in the document, depending on the version, as shown below:

- © NXP N.V. (year). All rights reserved or © Koninklijke Philips Electronics N.V. (year). All rights reserved

Should be replaced with:

- © Nexperia B.V. (year). All rights reserved.

If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia



Low capacitance bidirectional double ESD protection diode Rev. 03 — 9 February 2009 Product data she

Product data sheet

Product profile 1.

1.1 General description

Low capacitance bidirectional double ElectroStatic Discharge (ESD) protection diode in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package designed to protect two data lines from the damage caused by ESD and other transients.

1.2 Features

- Bidirectional ESD protection of two lines
- Low diode capacitance
- Max. peak pulse power: P_{PP} = 130 W at t_p = 8/20 μs
- Low clamping voltage: V_{CL} = 14 V at I_{PP} = 12 A
- Ultra low leakage current: I_{RM} = 5 nA at V_{RWM} = 5 V
- ESD protection up to 30 kV
- IEC 61000-4-2; level 4 (ESD)
- IEC 61000-4-5 (surge); I_{PP} = 12 A at t_p = 8/20 μs

1.3 Applications

- Cellular handsets and accessories
- Portable electronics
- Computers and peripherals
- Communication systems
- Audio and video equipment

1.4 Quick reference data

Table 1. Quick reference data

 $T_{amb} = 25 \circ C$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{RWM}	reverse standoff voltage		-	-	5	V
C _d	diode capacitance	f = 1 MHz; V _R = 0 V	-	35	45	pF



Low capacitance bidirectional double ESD protection diode

2. Pinning information

Table 2.	Pinning		
Pin	Description	Simplified outline	Graphic symbol
1	cathode 1		
2	cathode 2		
3	double cathode	1 2	
			sym031

3. Ordering information

Table 3. Orde	Ordering information		
Type number Package			
	Name	Description	Version
PESD5V0S2BT	-	plastic surface-mounted package; 3 leads	SOT23

4. Marking

Table 4. Marking	
Type number	Marking code ^[1]
PESD5V0S2BT	*G5

- [1] * = -: made in Hong Kong
 - * = p: made in Hong Kong
 - * = t: made in Malaysia
 - * = W: made in China

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per diode					
P _{PP}	peak pulse power	$t_p = 8/20 \ \mu s$	[1][2] _	130	W
I _{PP}	peak pulse current	$t_p = 8/20 \ \mu s$	[1][2] _	12	А
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

[1] Non-repetitive current pulse 8/20 µs exponential decay waveform.

[2] Measured from pin 1 to 3 or pin 2 to 3.

Table 6.	ESD maximum ratings	5
----------	---------------------	---

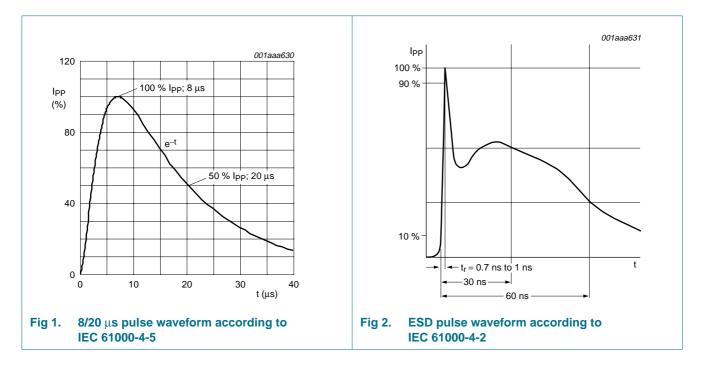
Symbol	Parameter	Conditions	I	Min	Max	Unit
V_{ESD}	electrostatic discharge voltage	IEC 61000-4-2 (contact discharge)	<u>[1][2]</u> .	-	30	kV
		MIL-STD-883 (human body model)	-	-	10	kV

[1] Device stressed with ten non-repetitive ESD pulses.

[2] Measured from pin 1 to 3 or pin 2 to 3.

Table 7. ESD standards compliance

Standard	Conditions
IEC 61000-4-2; level 4 (ESD)	> 15 kV (air); > 8 kV (contact)
MIL-STD-883; class 3 (human body model)	> 4 kV



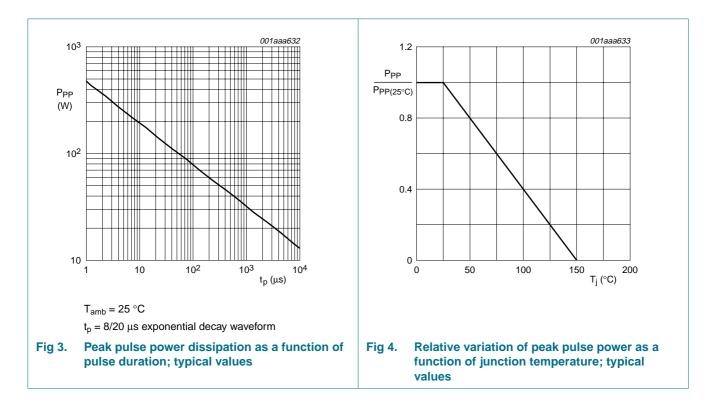
PESD5V0S2BT_3

6. Characteristics

Table 8. $T_{amb} = 25$	Electrical characteristics °C unless otherwise specified	d.					
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
Per diode)						
V _{RWM}	reverse standoff voltage			-	-	5	V
I _{RM}	reverse leakage current	$V_{RWM} = 5 V$		-	5	100	nA
V _{CL}	clamping voltage	I _{PP} = 1 A	[1][2]	-	-	10	V
		I _{PP} = 12 A	[1][2]	-	-	14	V
V_{BR}	breakdown voltage	I _R = 1 mA		5.5	-	9.5	V
r _{dif}	differential resistance	I _R = 1 mA		-	-	50	Ω
C _d	diode capacitance	f = 1 MHz; $V_R = 0 V$		-	35	45	pF

[1] Non-repetitive current pulse 8/20 µs exponential decay waveform.

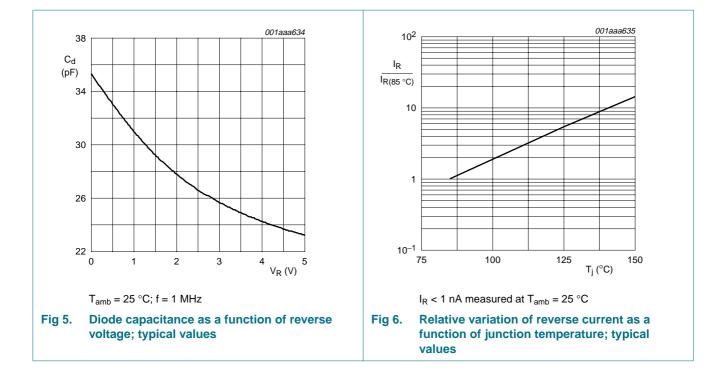
[2] Measured from pin 1 to 3 or pin 2 to 3.



NXP Semiconductors

PESD5V0S2BT

Low capacitance bidirectional double ESD protection diode

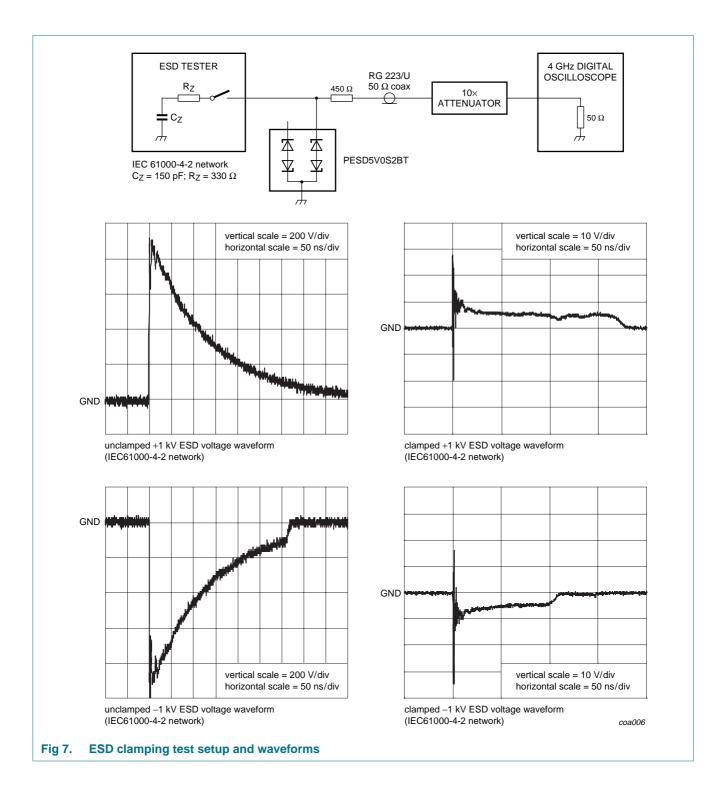


PESD5V0S2BT_3

NXP Semiconductors

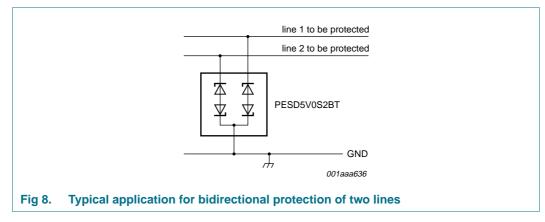
PESD5V0S2BT

Low capacitance bidirectional double ESD protection diode



7. Application information

The PESD5V0S2BT is designed for the bidirectional protection of two lines from the damage caused by ElectroStatic Discharge (ESD) and surge pulses. The PESD5V0S2BT may be used on lines where the signal polarities are both, positive and negative with respect to ground. The PESD5V0S2BT provides a surge capability of 130 W per line for an 8/20 µs waveform.



Circuit board layout and protection device placement:

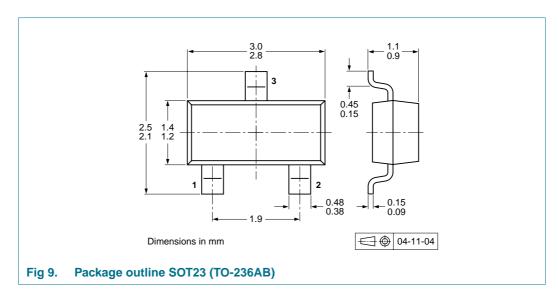
Circuit board layout is critical for the suppression of ESD, Electrical Fast Transient (EFT) and surge transients. The following guidelines are recommended:

- 1. Place the PESD5V0S2BT as close to the input terminal or connector as possible.
- 2. The path length between the PESD5V0S2BT and the protected line should be minimized.
- 3. Keep parallel signal paths to a minimum.
- 4. Avoid running protected conductors in parallel with unprotected conductors.
- 5. Minimize all Printed-Circuit Board (PCB) conductive loops including power and ground loops.
- 6. Minimize the length of the transient return path to ground.
- 7. Avoid using shared transient return paths to a common ground point.
- 8. Ground planes should be used whenever possible. For multilayer PCBs, use ground vias.

PESD5V0S2BT 3

Low capacitance bidirectional double ESD protection diode

8. Package outline



9. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

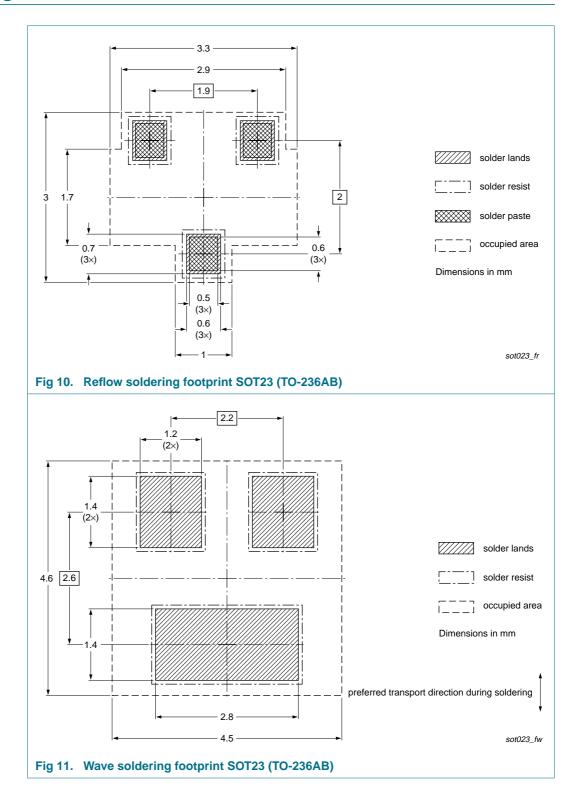
Type number	Package	Description	Packing	quantity
			3000	10000
PESD5V0S2BT	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235

[1] For further information and the availability of packing methods, see <u>Section 13</u>.

PESD5V0S2BT_3

Low capacitance bidirectional double ESD protection diode

10. Soldering



11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes			
PESD5V0S2BT_3	20090209	Product data sheet	-	PESD5V0S2BT_2			
Modifications:		of this data sheet has been of NXP Semiconductors.	n redesigned to comply v	vith the new identity			
	 Legal texts 	have been adapted to the	new company name whe	ere appropriate.			
 <u>Table 6</u>: ESD electro static discharge capability redefined to V_{ESD} electrostatic dis voltage 				ESD electrostatic discharge			
	• <u>Table 8</u> : V ₍₀	 <u>Table 8</u>: V_{(CL)R} clamping voltage redefined to V_{CL} 					
	<u>Figure 4</u> : figure notes removed						
	 Section 7 "Application information": updated 						
	 Figure 9: superseded by minimized package outline drawing 						
	 <u>Section 9 "Packing information"</u>: added 						
	Section 10	"Soldering": added					
	Section 12	"Legal information": update	ed				
PESD5V0S2BT_2	20040527	Product data sheet	-	PESD5V0S2BT_1			
PESD5V0S2BT 1	20040517	Product data sheet	-	_			

12. Legal information

12.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

12.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

12.3 Disclaimers

General — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in medical, military, aircraft, space or life support equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors accepts no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) may cause permanent damage to the device. Limiting values are stress ratings only and operation of the device at these or any other conditions above those given in the Characteristics sections of this document is not implied. Exposure to limiting values for extended periods may affect device reliability.

Terms and conditions of sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at http://www.nxp.com/profile/terms, including those pertaining to warranty, intellectual property rights infringement and limitation of liability, unless explicitly otherwise agreed to in writing by NXP Semiconductors. In case of any inconsistency or conflict between information in this document and such terms and conditions, the latter will prevail.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

12.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

13. Contact information

For more information, please visit: http://www.nxp.com

For sales office addresses, please send an email to: salesaddresses@nxp.com

NXP Semiconductors

PESD5V0S2BT

Low capacitance bidirectional double ESD protection diode

14. Contents

founded by

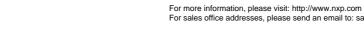
PHILIPS

1	Product profile 1
1.1	General description
1.2	Features
1.3	Applications 1
1.4	Quick reference data
2	Pinning information 2
3	Ordering information 2
4	Marking 2
5	Limiting values 2
6	Characteristics 4
7	Application information
8	Package outline 8
9	Packing information 8
10	Soldering 9
11	Revision history 10
12	Legal information 11
12.1	Data sheet status 11
12.2	Definitions 11
12.3	Disclaimers
12.4	Trademarks 11
13	Contact information 11
14	Contents 12

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.

© NXP B.V. 2009.

All rights reserved.



For sales office addresses, please send an email to: salesaddresses@nxp.com Date of release: 9 February 2009 Document identifier: PESD5V0S2BT_3